

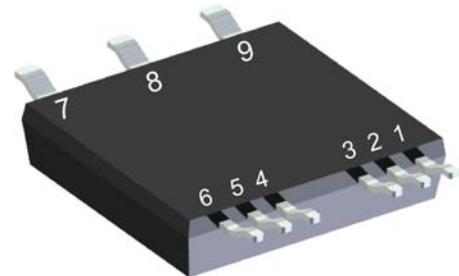
Standard Rectifier

3~ Rectifier
$V_{RRM} = 1800 \text{ V}$
$I_{DAV} = 90 \text{ A}$
$I_{FSM} = 350 \text{ A}$

ISOPLUS™
 Surface Mount Power Device
 3~ Rectifier Bridge

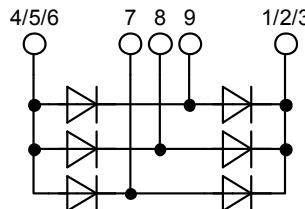
Part number

DMA90U1800LB



Backside: isolated

E72873



Features / Advantages:

- Rectifier diode
- Isolated back surface
- Low coupling capacity between pins and heatsink
- Enlarged creepage towards heatsink
- Application friendly pinout
- Low inductive current path
- High reliability

Applications:

- Line rectifying 50/60 Hz
- Drives
- SMPS
- UPS

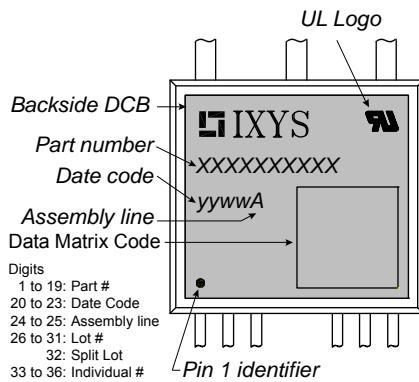
Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ C$			1800	V
I_R	reverse current	$V_R = 1800 V$ $V_R = 1800 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		40 1.5	μA mA
V_F	forward voltage drop	$I_F = 30 A$ $I_F = 90 A$ $I_F = 30 A$ $I_F = 90 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$		1.26 1.79 1.20 1.93	V V
I_{DAV}	bridge output current	$T_C = 110^\circ C$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 175^\circ C$		90	A
V_{FO} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ C$		0.81 12.7	V $m\Omega$
R_{thJC}	thermal resistance junction to case				1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.4	K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		135	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		350 380	A
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		300 320	A
I^2t	value for fusing	$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 45^\circ C$ $V_R = 0 V$		615 600	A^2s A^2s
		$t = 10 ms; (50 Hz)$, sine $t = 8,3 ms; (60 Hz)$, sine	$T_{VJ} = 150^\circ C$ $V_R = 0 V$		450 425	A^2s A^2s
C_J	junction capacitance	$V_R = 400 V; f = 1 MHz$	$T_{VJ} = 25^\circ C$		11	pF

Package SMPD		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				8.5		g
F_c	mounting force with clip		40		130	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	1.6			mm
$d_{Spb/Abp}$		terminal to backside	4.0			mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000 2500			V

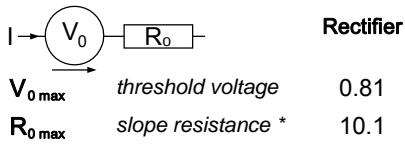
**Part number**

D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 90 = Current Rating [A]
 U = 3~ Rectifier Bridge
 1800 = Reverse Voltage [V]
 LB = SMPD-B

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA90U1800LB	DMA90U1800LB	Blister	45	511747
Alternative	DMA90U1800LB-TRR	DMA90U1800LB	Tape & Reel	200	511740

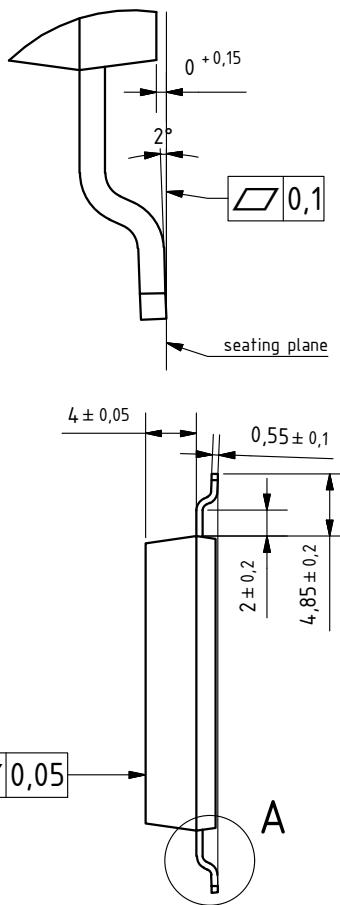
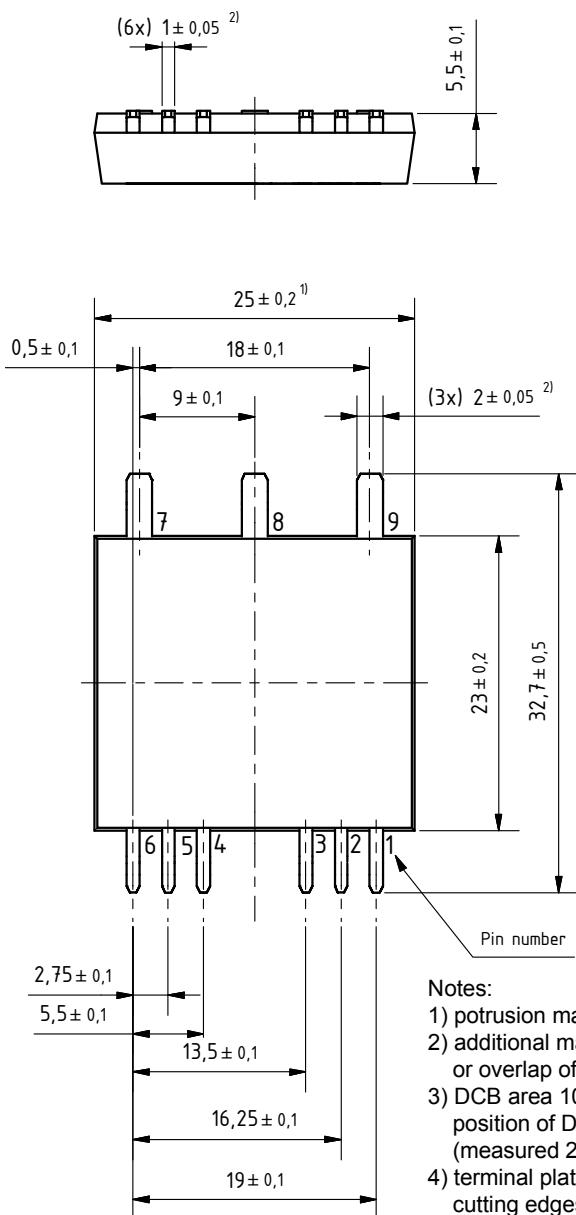
Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 175$ °C

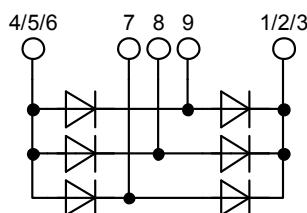
Outlines SMPD

A (8 : 1)



Notes:

- 1) potrusion may add 0.2 mm max. on each side
- 2) additional max. 0.05 mm per side by punching misalignement or overlap of dam bar or bending compression
- 3) DCB area 10 to 50 µm convex; position of DCB area in relation to plastic rim: ±25 µm (measured 2 mm from Cu rim)
- 4) terminal plating: 0.2 - 1 µm Ni + 10 - 25 µm Sn (gal v.) cutting edges may be partially free of plating



Rectifier

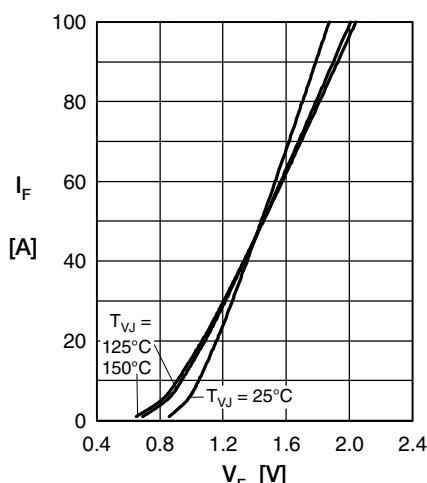


Fig. 1 Forward current vs. voltage drop per diode

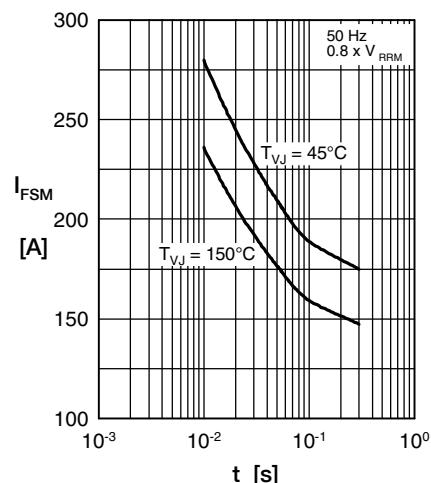


Fig. 2 Surge overload current vs. time per diode

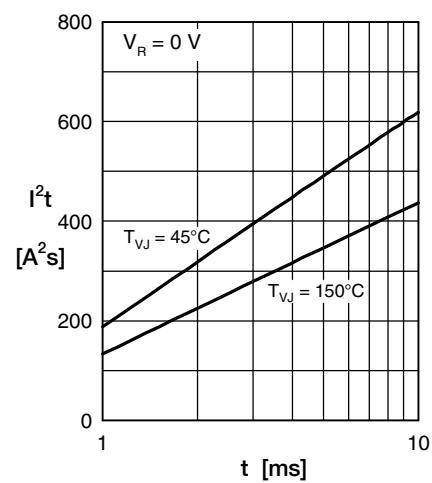
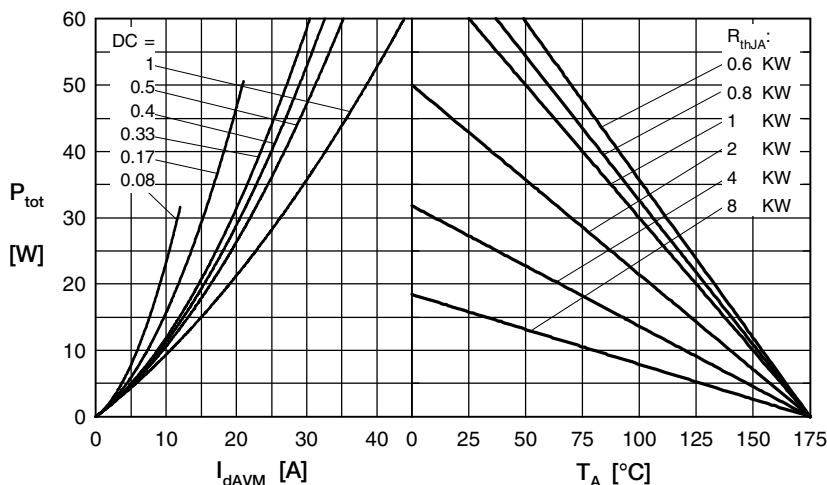
Fig. 3 I^2t vs. time per diode

Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

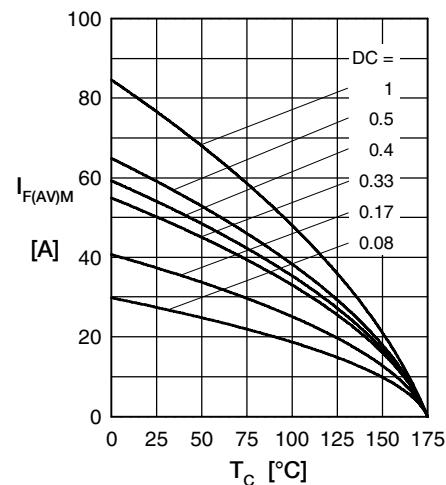


Fig. 5 Max. forward current vs. case temperature per diode

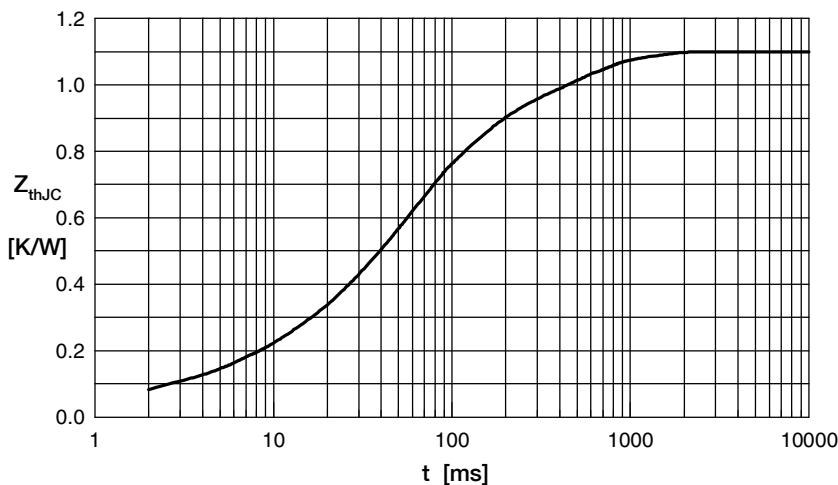


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.030	0.0003
2	0.072	0.0045
3	0.092	0.0530
4	0.606	0.0520
5	0.300	0.4000

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